



NCE N-Channel Super Trench Power MOSFET

Description

The NCEP02580D uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{\text{DS(ON)}}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

General Features

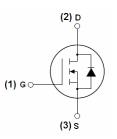
- V_{DS} =250V, I_{D} =80A $R_{DS(ON)}$ <18.5m Ω @ V_{GS} =10V
- Excellent gate charge x R_{DS(on)} product
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

100% UIS TESTED!

100% ΔVds TESTED!



Schematic diagram



Marking and pin assignment



TO-263-2L top view

Package Marking and Ordering Information

| Device Marking | Device | Device Package | Reel Size | Tape width | Quantity |
|----------------|------------|----------------|-----------|------------|----------|
| NCEP02580D | NCEP02580D | TO-263-2L | - | - | - |

Absolute Maximum Ratings (T_C=25 ℃unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|--|-----------------------|------------|--------------|
| Drain-Source Voltage | VDS | 250 | V |
| Gate-Source Voltage | V _G S | ±20 | V |
| Drain Current-Continuous | I _D | 80 | Α |
| Drain Current-Continuous(T _C =100 °C) | I _D (100℃) | 56.6 | А |
| Pulsed Drain Current | I _{DM} | 320 | А |
| Maximum Power Dissipation | P _D | 300 | W |
| Derating factor | | 2 | W/°C |
| Single pulse avalanche energy (Note 5) | E _{AS} | 1200 | mJ |
| Operating Junction and Storage Temperature Range | T_{J}, T_{STG} | -55 To 175 | $^{\circ}$ C |



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Thermal Characteristic

| Thermal Resistance, Junction-to-Case (Note 2) | R _{eJC} | 0.5 | °C/W |
|---|------------------|-----|------|
|---|------------------|-----|------|

Electrical Characteristics (T_C=25°C unless otherwise noted)

| Parameter | Symbol | Condition | Min | Тур | Max | Unit |
|------------------------------------|---------------------|--|---|------|------|------|
| Off Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0V I _D =250µA | 250 | | - | V |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} =250V,V _{GS} =0V | V _{DS} =250V,V _{GS} =0V - | | 1 | μΑ |
| Gate-Body Leakage Current | I _{GSS} | V_{GS} =±20 V , V_{DS} =0 V | - | - | ±100 | nA |
| On Characteristics (Note 3) | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | $V_{DS}=V_{GS}$, $I_{D}=250\mu A$ | 2.5 | | 4.5 | V |
| Drain-Source On-State Resistance | R _{DS(ON)} | V _{GS} =10V, I _D =40A | - | 16 | 18.5 | mΩ |
| Forward Transconductance | g FS | V _{DS} =10V,I _D =40A | 70 | - | - | S |
| Dynamic Characteristics (Note4) | | | | | | |
| Input Capacitance | C _{lss} | \/ -405\/\/ -0\/ | - | 5400 | - | PF |
| Output Capacitance | C _{oss} | V_{DS} =125V, V_{GS} =0V, F=1.0MHz | - | 329 | - | PF |
| Reverse Transfer Capacitance | C _{rss} | F=1.UIVIFIZ | - | 12 | - | PF |
| Switching Characteristics (Note 4) | | | | | | |
| Turn-on Delay Time | t _{d(on)} | | - | 18 | - | nS |
| Turn-on Rise Time | t _r | V_{DD} =125 V , I_D =40 A | - | 26 | - | nS |
| Turn-Off Delay Time | t _{d(off)} | V_{GS} =10 V , R_{G} =4.7 Ω | - | 41 | - | nS |
| Turn-Off Fall Time | t _f | | - | 11 | - | nS |
| Total Gate Charge | Qg | \/ -405\/ -404 | - | 76.7 | | nC |
| Gate-Source Charge | Q _{gs} | V_{DS} =125V, I_{D} =40A, V_{GS} =10V | - | 22.7 | | nC |
| Gate-Drain Charge | Q _{gd} | V _{GS} -10V | - | 20 | | nC |
| Drain-Source Diode Characteristics | | | | | | |
| Diode Forward Voltage (Note 3) | V _{SD} | V _{GS} =0V,I _S =80A | - | | 1.2 | V |
| Diode Forward Current (Note 2) | Is | | - | - | 80 | Α |
| Reverse Recovery Time | t _{rr} | T _J = 25°C, I _F = 40 | - | 140 | | nS |
| Reverse Recovery Charge | Qrr | $di/dt = 100A/\mu s^{(Note3)}$ | - | 600 | | nC |
| | | | | | | |

Notes:

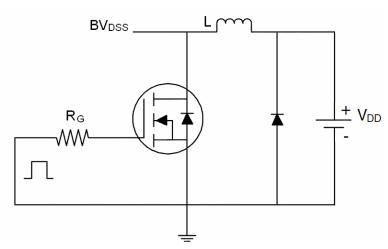
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t \leq 10 sec.
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25 $^{\circ}\text{C}$,V_DD=50V,V_G=10V,L=0.5mH,Rg=25 Ω



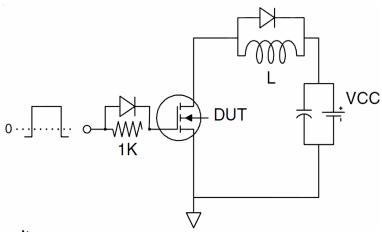
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Test Circuit

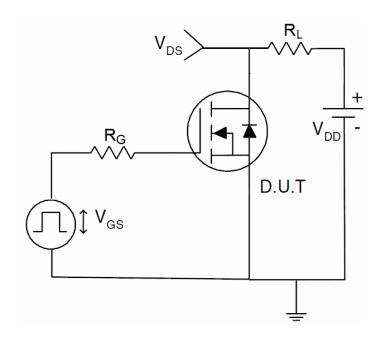
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit







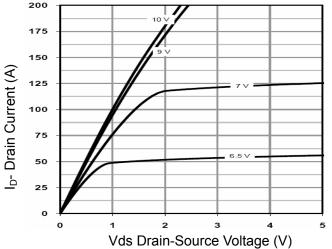


Figure 1 Output Characteristics

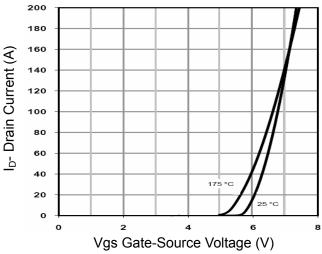


Figure 2 Transfer Characteristics

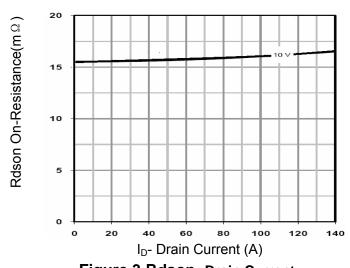


Figure 3 Rdson- Drain Current

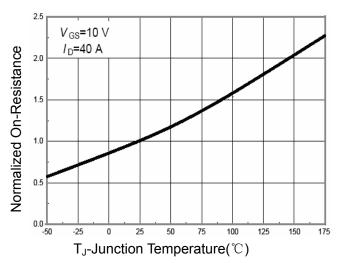


Figure 4 Rdson-JunctionTemperature

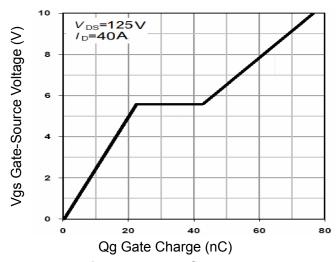


Figure 5 Gate Charge

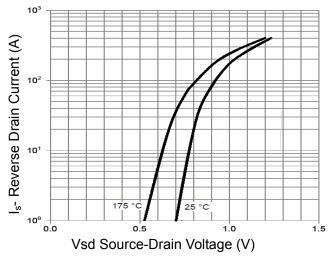
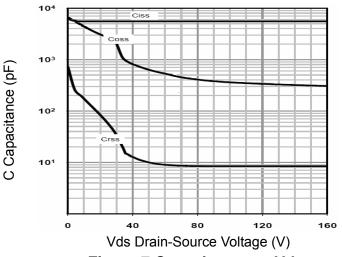


Figure 6 Source- Drain Diode Forward





280

280

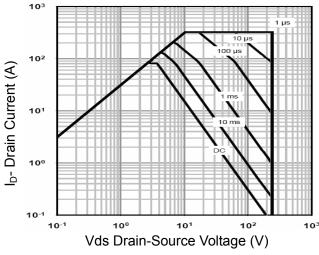
(M)

240

Loop to the dissipation of the displacement of the di

Figure 7 Capacitance vs Vds

Figure 9 Power De-rating



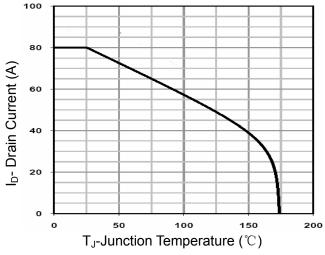
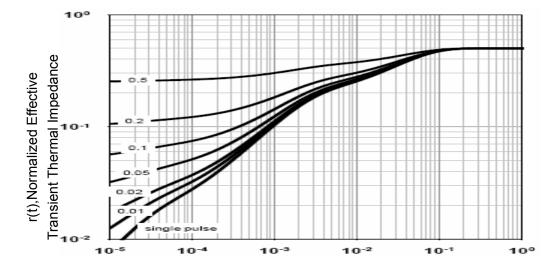


Figure 8 Safe Operation Area

Figure 10 Current De-rating

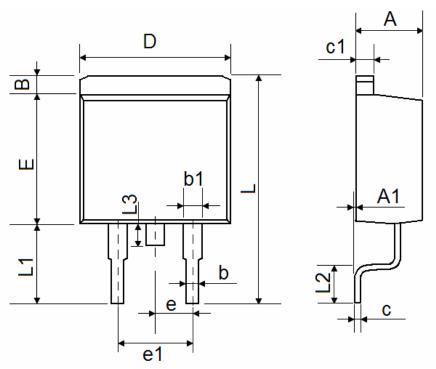


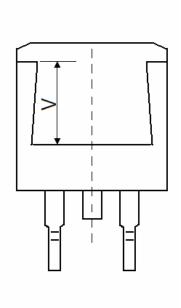
Square Wave Pluse Duration(sec)

Figure 11 Normalized Maximum Transient Thermal Impedance



TO-263-2L Package Information





| Symbol | Dimensions | In Millimeters | Dimensions In Inches | | |
|--------|------------|----------------|----------------------|-------|--|
| Symbol | Min. | Max. | Min. | Max. | |
| Α | 4.470 | 4.670 | 0.176 | 0.184 | |
| A1 | 0.000 | 0.150 | 0.000 | 0.006 | |
| В | 1.170 | 1.370 | 0.046 | 0.054 | |
| b | 0.710 | 0.910 | 0.028 | 0.036 | |
| b1 | 1.170 | 1.370 | 0.046 | 0.054 | |
| С | 0.310 | 0.530 | 0.012 | 0.021 | |
| c1 | 1.170 | 1.370 | 0.046 | 0.054 | |
| D | 10.010 | 10.310 | 0.394 | 0.406 | |
| Е | 8.500 | 8.900 | 0.335 | 0.350 | |
| е | 2.540 TYP. | | 0.100 TYP. | | |
| e1 | 4.980 | 5.180 | 0.196 | 0.204 | |
| L | 15.050 | 15.450 | 0.593 | 0.608 | |
| L1 | 5.080 | 5.480 | 0.200 | 0.216 | |
| L2 | 2.340 | 2.740 | 0.092 | 0.108 | |
| L3 | 1.300 | 1.700 | 0.051 | 0.067 | |
| V | 5.600 |) REF | 0.220 | REF | |



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